

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
100V	2.7mΩ@10V	220A

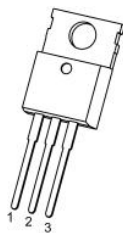
Feature

- Fast Switching
- Low Gate Charge and Rdson
- Advanced Split Gate Trench Technology
- 100% Single Pulse avalanche energy Test

Applications

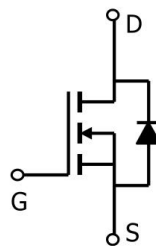
- PWM Application
- Hard switched and high frequency circuits
- Power Management

Package

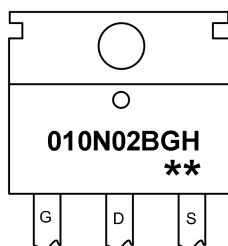


TO-220-3L-C(1:G 2:D 3:S)

Circuit diagram



Marking



010N02BGH
**

=Device Code
=Week Code

**Absolute maximum ratings (Ta=25°C, unless otherwise noted)**

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current (Tc=25°C)	I_D	220	A
Pulsed Drain Current	I_{DM}	880	A
Single Pulse Avalanche Energy ¹	E_{AS}	1458	mJ
Total Power Dissipation ² (Tc=25°C)	P_D	300	W
Thermal Resistance Junction-Case	$R_{\theta JC}$	0.41	°C/W
Storage Temperature Range	T_{STG}	-55 to 150	°C
Operating Junction Temperature Range	T_J	-55 to 150	°C

Electrical characteristics (Ta=25°C, unless otherwise noted)

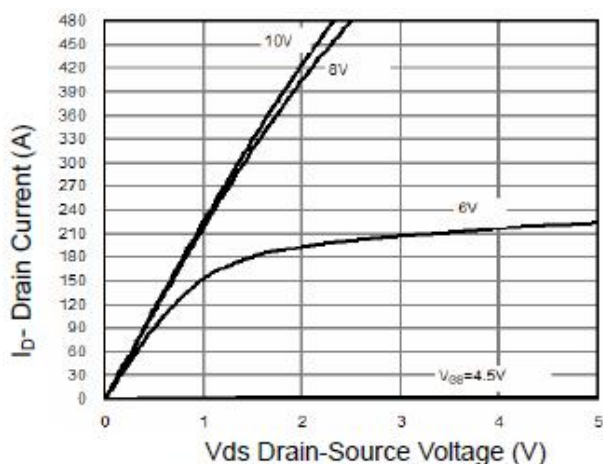
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	VGS=0V , ID=250uA	100	---	---	V
Drain-Source Leakage Current	IDSS	VDS=80V , VGS=0V , TJ=25℃	---	---	1	uA
Gate-Source Leakage Current	IGSS	VGS=±20V , VDS=0V	---	---	±100	nA
Gate Threshold Voltage	VGS(th)	VGS=VDS , ID =250uA	2.7	3.2	4.3	V
Static Drain-Source On-Resistance	RDS(ON)	VGS=10V , ID=125A	---	2.7	3.5	mΩ
Dynamic characteristics						
Input Capacitance	Ciss	VDS=50V , VGS=0V , f=1MHz	---	11531	---	pF
Output Capacitance	Coss		---	1489	---	
Reverse Transfer Capacitance	Crss		---	72	---	
Switching Characteristics						
Total Gate Charge (4.5V)	Qg	VDS=50V , VGS=10V , ID=125A	---	158	---	nC
Gate-Source Charge	Qgs		---	51	---	
Gate-Drain Charge	Qgd		---	27	---	
Turn-On Delay Time	Td(on)	VDD=50V, VGS=10V , RG=1.6Ω, ID=125A	---	25	---	ns
Rise Time	Tr		---	75	---	
Turn-Off Delay Time	Td(off)		---	89	---	
Fall Time	Tf		---	29	---	
Diode Characteristics						
Diode Forward Voltage2	VSD	VGS=0V , IS=1A , TJ=25℃	---	---	1.2	V

Note :

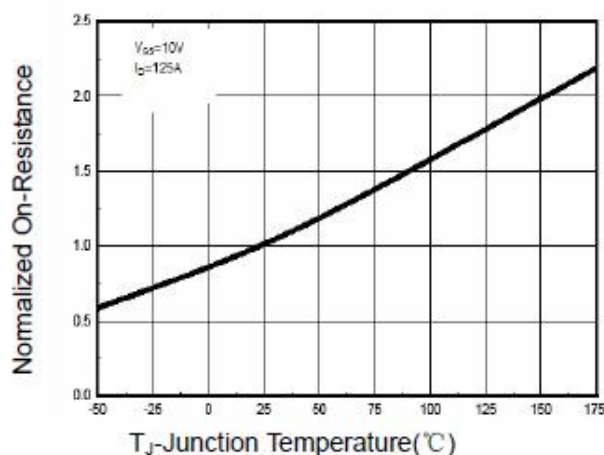
- The EAS data shows Max. rating . The test condition is $V_{DD}=50V$, $V_{GS}=10V$, $L=0.5mH$, $R_G=25\Omega$
- The power dissipation is limited by 150°C junction temperature



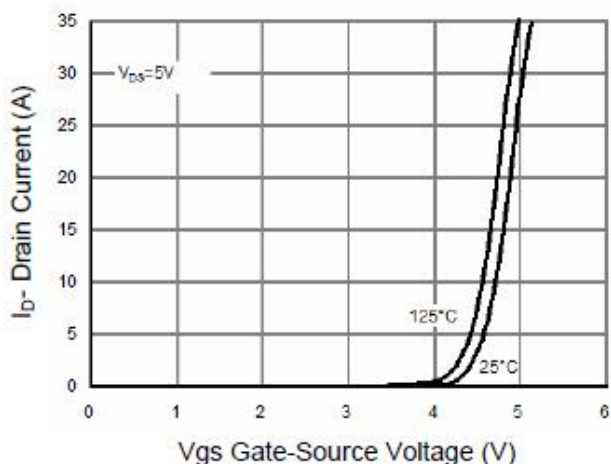
Typical Characteristics



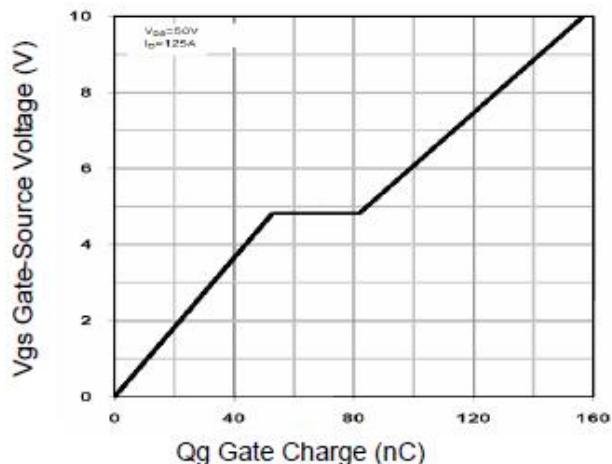
Output Characteristics



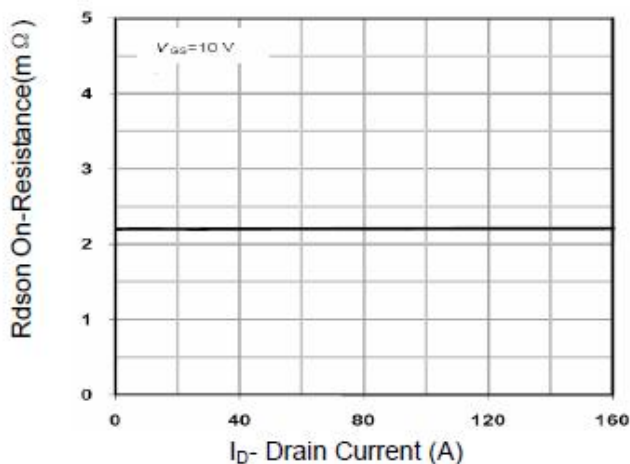
$R_{DS(on)}$ -Junction Temperature



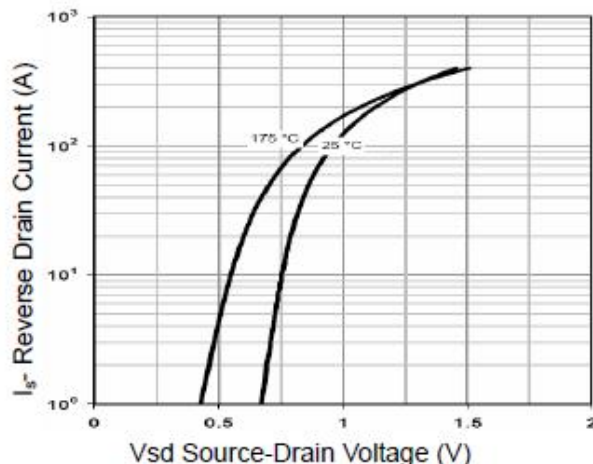
Transfer Characteristics



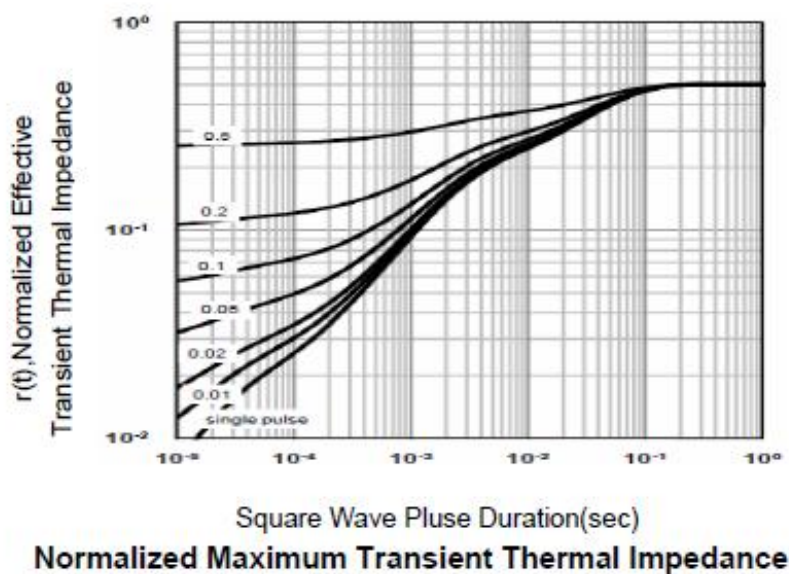
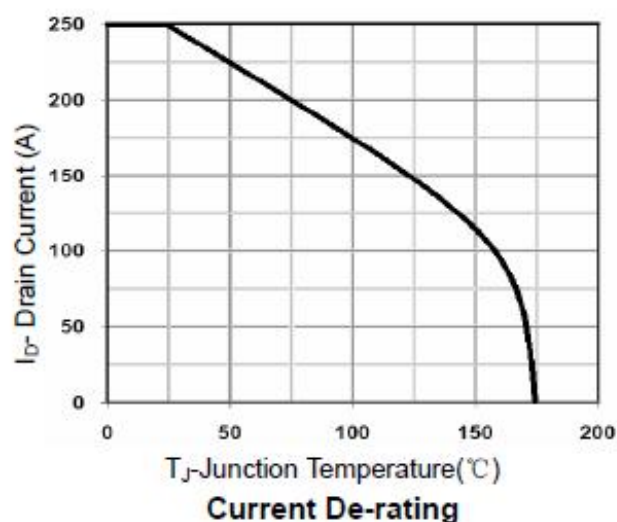
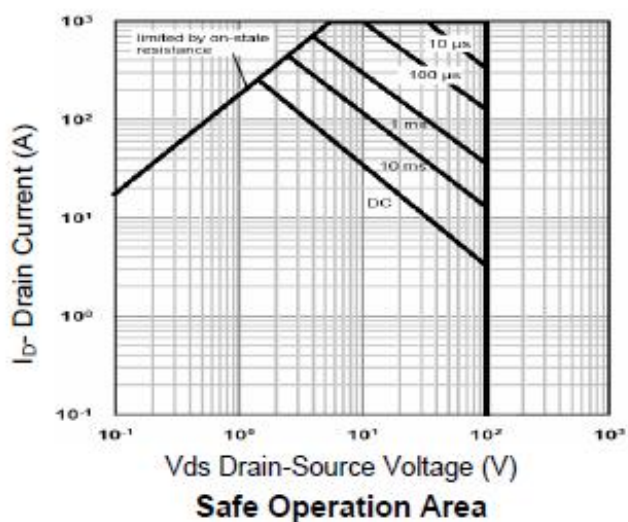
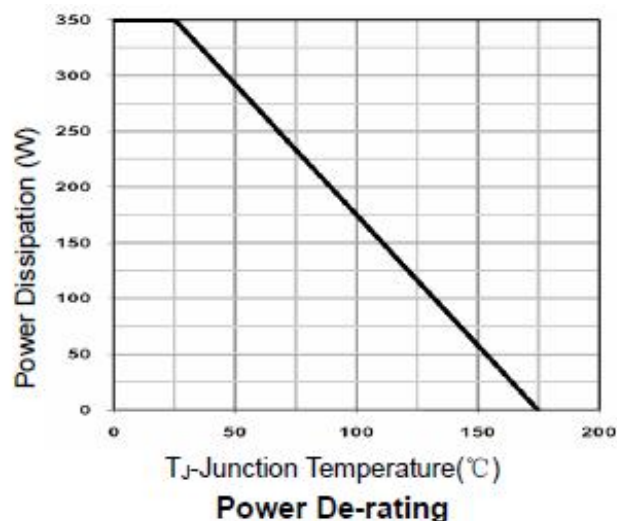
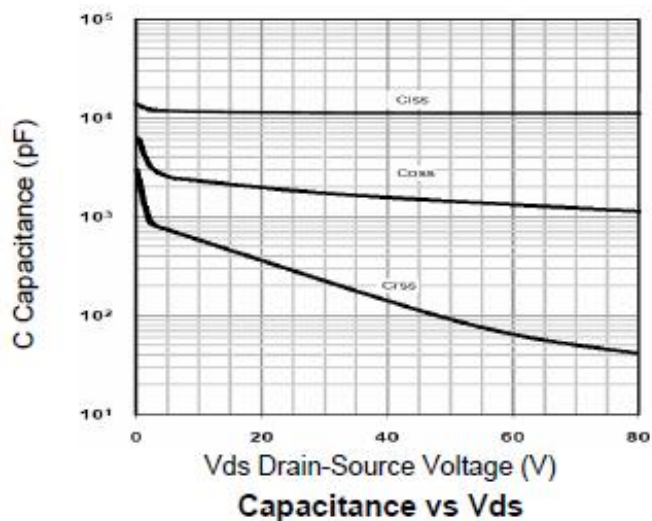
Gate Charge



$R_{DS(on)}$ - Drain Current

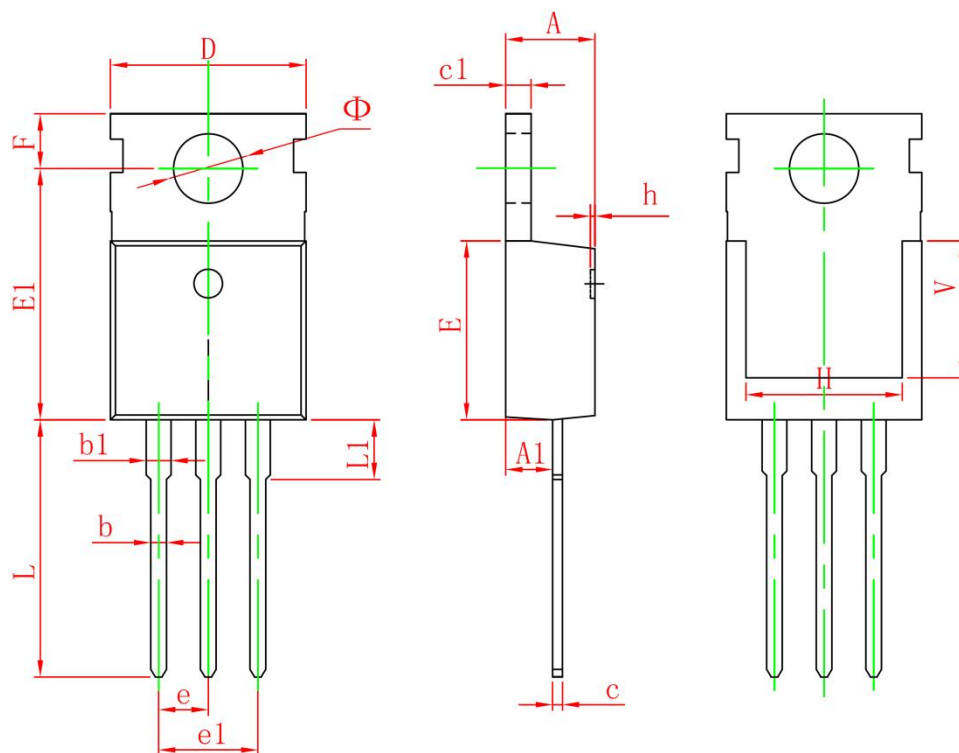


Source- Drain Diode Forward





TO-220-3L-C Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.950	9.750	0.352	0.384
E1	12.650	13.050	0.498	0.514
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	6.900 REF.		0.276 REF.	
Φ	3.400	3.800	0.134	0.150